

N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16321Q5

FEATURES

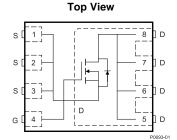
- Optimized for 5V Gate Drive
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- SON 5mm × 6mm Plastic Package

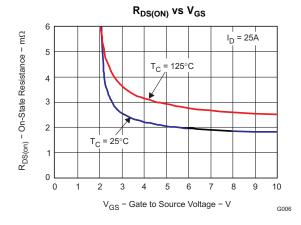
APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage 25			٧
Q_g	Gate Charge Total (4.5V) 14			nC
Q_{gd}	Gate Charge Gate to Drain 2.5			nC
		$V_{GS} = 3V$	2.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V 2.1		mΩ
		V _{GS} = 8V 1.9		mΩ
V _{GS(th)}	Threshold Voltage	1.1		V

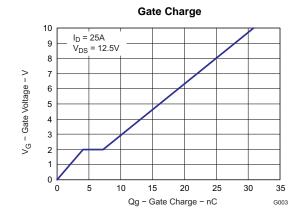
ORDERING INFORMATION

Device Package		Media	Qty	Ship	
CSD16321Q5	SON 5 x 6 Plastic Package	13-inch reel	2500	Tape and Reel	

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT						
V_{DS}	Drain to Source Voltage	25	٧						
V_{GS}	Gate to Source Voltage	+10 / -8	٧						
	Continuous Drain Current, T _C = 25°C	100	Α						
I _D	Continuous Drain Current(1)	31	Α						
I_{DM}	Pulsed Drain Current, T _A = 25°C(2)	200	Α						
P_D	Power Dissipation(1)	3.1	W						
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C						
E _{AS}	Avalanche Energy, single pulse $I_D=66A,L=0.1mH,R_G=25\Omega$	218	mJ						

- (1) Typical $\rm R_{\theta JA} = 39^{\circ} C/W$ on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics	·				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V			1	μА
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = +10 / -8V			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9	1.1	1.4	V
		$V_{GS} = 3V, I_D = 25A$		2.8	3.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 25A$		2.1	2.6	mΩ
		$V_{GS} = 8V, I_D = 25A$		1.9	2.4	mΩ
9 _{fs}	Transconductance	$V_{DS} = 12.5V, I_D = 25A$		150		S
Dynami	c Characteristics		, -			
C _{iss}	Input Capacitance			2360	3100	рF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ f = 1MHz		1700	2200	рF
C _{rss}	Reverse Transfer Capacitance	1 - 10112		115	150	pF
R_G	Series Gate Resistance			1.5	3	Ω
Qg	Gate Charge Total (4.5V)			14	19	nC
Q _{gd}	Gate Charge Gate to Drain	V _{DS} = 12.5V,		2.5		nC
Q _{gs}	Gate Charge Gate to Source	I _D = 25A		4		nC
Q _{g(th)}	Gate Charge at Vth			2.1		nC
Q _{oss}	Output Charge	V _{DS} = 15V, V _{GS} = 0V		36		nC
t _{d(on)}	Turn On Delay Time			9		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		15		ns
t _{d(off)}	Turn Off Delay Time	$I_D = 25A$, $R_G = 2\Omega$		27		ns
t _f	Fall Time			17		ns
Diode C	haracteristics				*	
V_{SD}	Diode Forward Voltage	I _{SD} = 25A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	$V_{DD} = 13V$, $I_F = 25A$, $di/dt = 300A/\mu s$		33		nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 25A$, $di/dt = 300A/\mu s$		32		ns

THERMAL CHARACTERISTICS

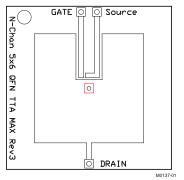
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
R ₀ JC	Thermal Resistance Junction to Case ⁽¹⁾			1.1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			48	°C/W

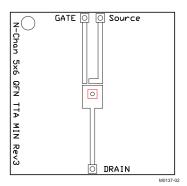
⁽¹⁾ $R_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in .060 inch thick FR4 board. $R_{\theta JC}$ is specified by design while $R_{\theta JA}$ is determined by the user's board design.

(2) Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.





Max $R_{\theta JA} = 48^{\circ} C/W$ when mounted on 1 inch² of 2 oz. Cu.



Max $R_{\theta JA} = 115^{\circ} C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

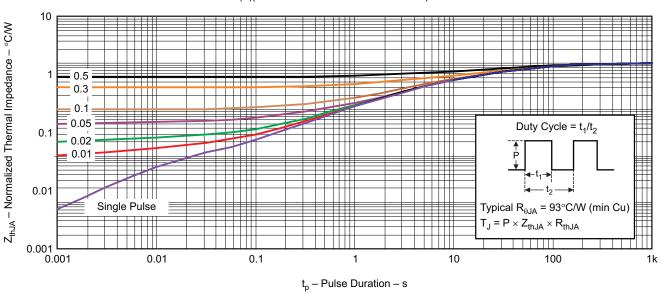


Figure 1. Transient Thermal Impedance

G012



TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

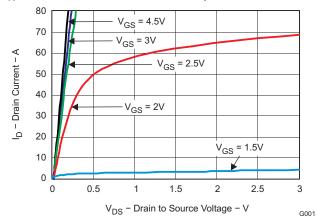


Figure 2. Saturation Characteristics

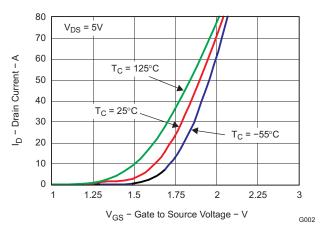


Figure 3. Transfer Characteristics

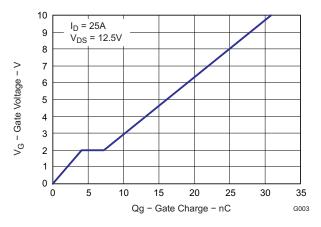


Figure 4. Gate Charge

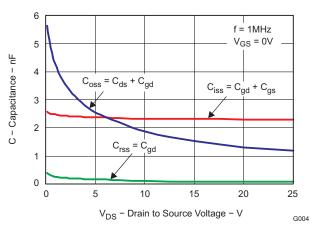


Figure 5. Capacitance



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

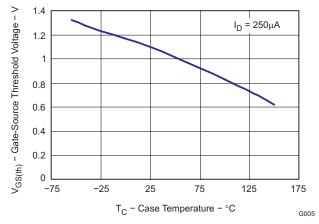


Figure 6. Threshold Voltage vs. Temperature

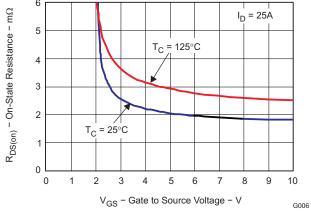


Figure 7. On Resistance vs. Gate Voltage

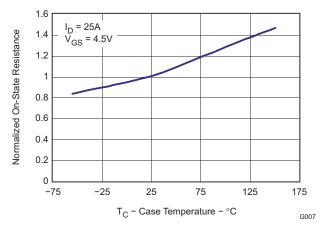


Figure 8. On Resistance vs. Temperature

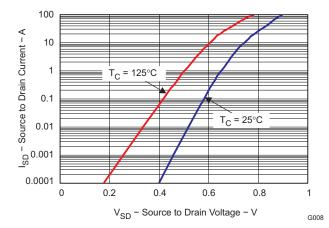


Figure 9. Typical Diode Forward Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

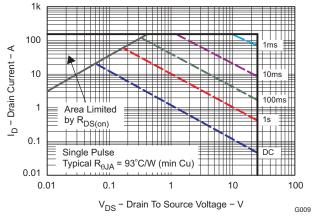


Figure 10. Maximum Safe Operating Area

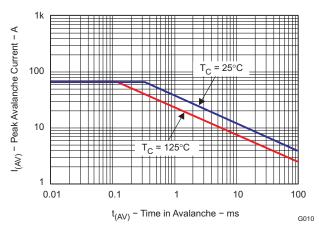


Figure 11. Single Pulse Unclamped Inductive Switching

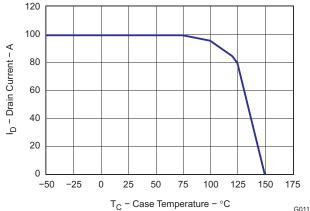
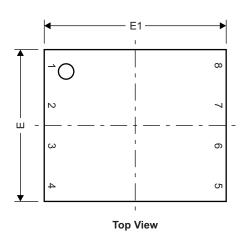


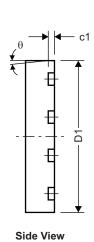
Figure 12. Maximum Drain Current vs. Temperature

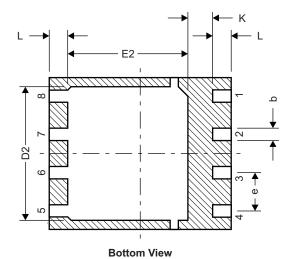


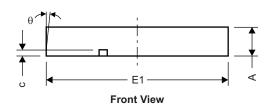
MECHANICAL DATA

Q5 Package Dimensions





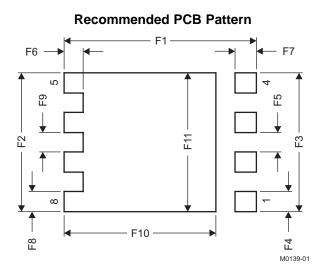




M0140-01

DIM	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
E	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.0	50	
K	0.760		0.030		
L	0.510	0.710	0.020	0.028	
θ	0.00				

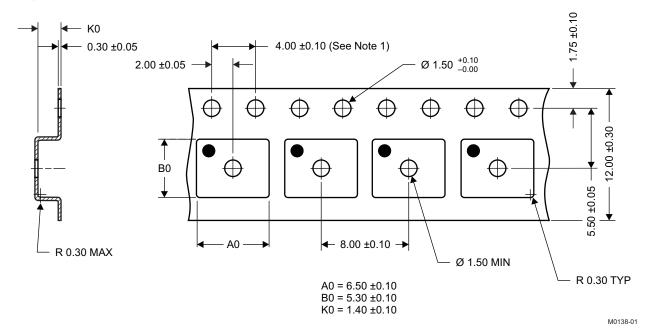




DIM	MILLIM	ETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. ThickNess: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



REVISION HISTORY

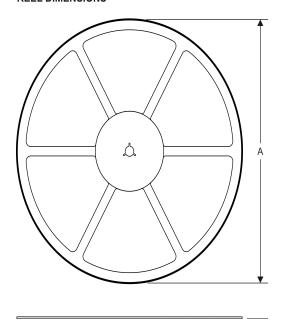
Changes from Original (August 2009) to Revision A	Page
Changed the labels on the Top View pinout image	1
• Changed Note 1 of the ABSOLUTE MAXIMUM RATINGS From: $R_{\theta JA} = 39^{\circ}\text{C/W}$ To: Typical $R_{\theta JA} = 39^{\circ}\text{C/W}$	1
 Changed Figure 1 text From: R_{θJA} = 92°C/W To: Typical R_{θJA} = 93°C/W 	3
 Changed Figure 10 text From: R_{θJA} = 92°C/W To: Typical R_{θJA} = 93°C/W 	6
Changed Figure 11 X-axis values	6
Changes from Revision A (Jaunary 2010) to Revision B	Page
 Changed R_{DS(on)} - V_{GS} = 3V, I_D = 25A MAX value From: 3.5 To: 3.8 	2
Deleted the Package Marking Information section	8

PACKAGE MATERIALS INFORMATION

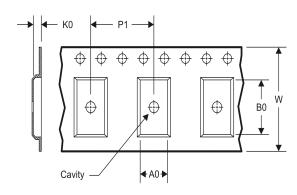
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

	Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
I	CSD16321Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

	Device	Package Type	kage Type Package Drawing		SPQ	Length (mm)	Width (mm)	Height (mm)
I	CSD16321Q5	SON	DQH	8	2500	335.0	335.0	32.0

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